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ROLL : 20 4TH YEAR 2ND SEMESTER

### VLSI

Q1 (a) In 1965, Gordon Moore predicted that the number of transistors on a die would grow exponentially doubling every 12 to 18 months. Moore, however, estimated that the possibilities of circuit and device cleverness were already becoming exhausted. The future developments, therefore, were to be based on bigger dice and finer dimensions. Accordingly, Moore revised his original growth rate estimate in 1975, and proposed that by the end of the decade, the number of components on the most complex chips would double about every two years.

#### Impact of Moore's Law:

There was an extremely rapid growth in the numbers of transistors being integrated into circuits on a single silicon chip. In 3 decades the number rose from tens to millions. Moore's Law brought significant developments to integration and scaling that were never imaginable before. But it also sucked all the talent to do mostly scaling (posting) integration type of engineering, instead of new innovations. Due to this, constraints on cost, verification, performance, area have now been reached.

(b) Verification is the predictive analysis to ensure that the synthesized design, when manufactured, will perform the given I/O function.

②

Verification is done before silicon development.

It is done at the time of product development for quality checking and bug fixing in synthesis phase. Verification is done at the physical

synthesis phase.

(c) Semiconductors are materials which have conductivity between conductors and non-conductors or insulators. Semiconductors are made from pure elements, typically silicon or germanium, or compounds such as gallium arsenide.

## Q2(a) Problems of BJT:

(3)

- BJTs have low thermal stability.
- BJTs have a low switching frequency.
- They have a very complex base control and so requires ~~skillful~~ skillful handling.
- They produce more noise.
- There is more power dissipation and current leakage.
- Power dissipation limits device density.
- BJTs are bulky requiring more space in the IC.

(b) There are two kinds of power dissipation in CMOS - static and dynamic. The static dissipation refers to the time when the CMOS is not in the process of switching states. The static power dissipation is very less because the current flowing through the IC is ~~near~~ nearly zero. But, there is dynamic loss as well. It is the loss which occurs while the circuit switches from one logic state to another. Some power is used to charge the capacitors as well which is known as load capacitance. All these losses together results in power dissipation in CMOS.

In static condition the current through a CMOS is zero. However there is a small amount of static power consumption due to reverse bias leakage between diffused regions and substrate of a CMOS. The source-drain diffusion and the n-well diffusion from parasitic diodes in the CMOS between n-well and substrate. These parasitic diodes contribute to power loss as they are reverse biased.

(c)  $\lambda$ -based design rules are design rules based on a single parameter  $\lambda$ . All paths in all layers will be dimensioned in  $\lambda$  units and subsequently  $\lambda$  can be allocated an appropriate value compatible with the feature size of the fabrication process.

#### Advantages:

- Simple for the designer.
- Wide acceptance
- Provide feature size independent way of setting out mask.
- If design rules are obeyed, masks will produce working circuits.
- Minimum feature size is defined as  $2\lambda$ .
- Used to preserve topological features on a chip.
- Prevents shorting, opens, contacts from slipping ~~out~~ of area to be contacted.

#### (d) Use of Silicon:

- Silicon allows a large variety of process steps to be possible without the problem of decomposition. (as in case of compound semiconductors)
- Silicon has a wider band gap than Ge thus a higher operating ~~temperature~~ temperature. ( $125^\circ\text{C} - 175^\circ\text{C}$  vs  $85^\circ\text{C}$ ).

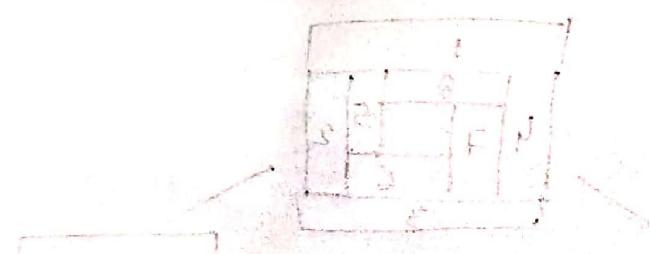
- Silicon readily forms a native oxide ( $\text{SiO}_2$ ). ⑤
- Silicon is cheap and abundant.

### Use of $\text{SiO}_2$

- $\text{SiO}_2$  is a high quality insulator.
- Protects and ~~passivates~~ underlying circuitry.
- Helps in patterning.
- Useful for dopant masking.



mask available for doping mask with which  
how it is worked and why mask like this is used for  
doping



~~Q3~~ Q3(a)

(6)

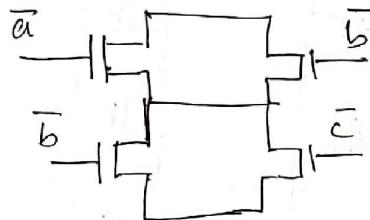
### Advantages of single complex cell.

- There is negligible power dissipation as static state power consumption of CMOS circuits is very small.
- As CMOS are voltage driven, one gate can drive many more inputs which results in higher fanout.
- Single cell complex designs are thermally stable. They can operate steadily ~~at~~ in a wide range of temperature.
- They are more immune to noise.

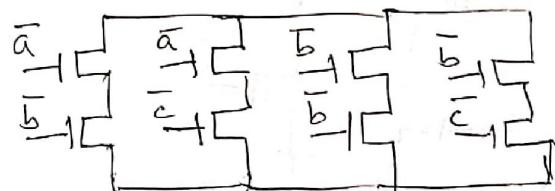
$$\text{f} = ab + bc = \overline{\overline{ab} + \overline{bc}} = \overline{(\overline{a}\overline{b}) \cdot (\overline{b}\overline{c})}$$

NMOS

$$= \overline{(\overline{a} + \overline{b}) \cdot (\overline{b} + \overline{c})} = \overline{(\overline{a}\overline{b} + \overline{a}\overline{c} + \overline{b} + \overline{b}\overline{c})}$$

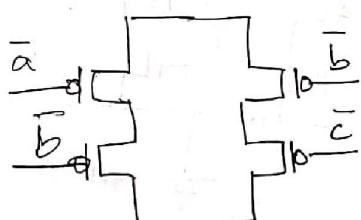


Parallel Series.

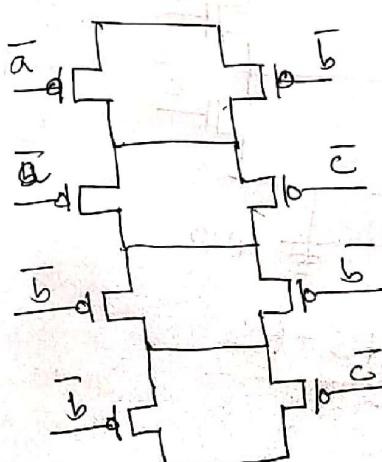


Series parallel.

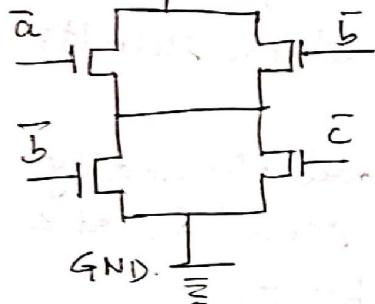
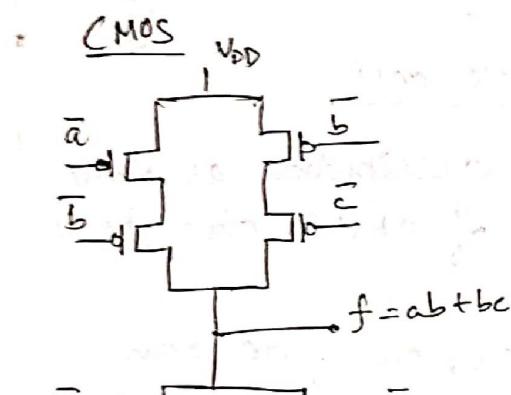
PMOS



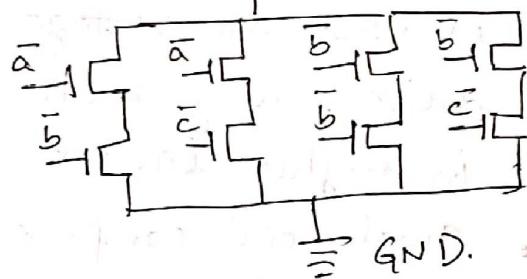
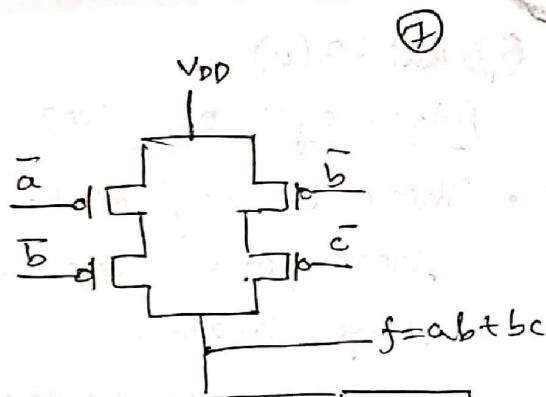
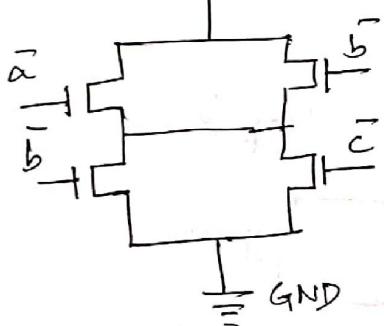
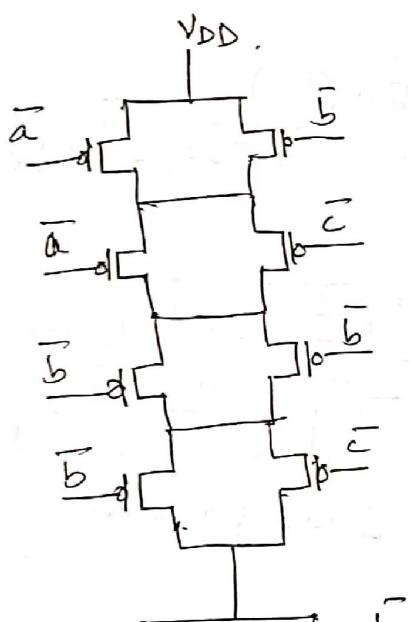
Series parallel



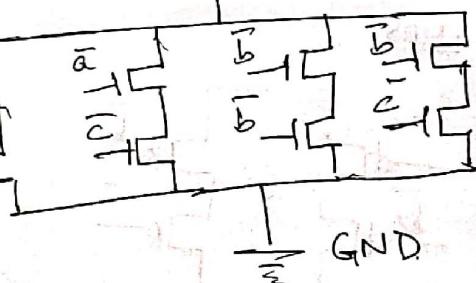
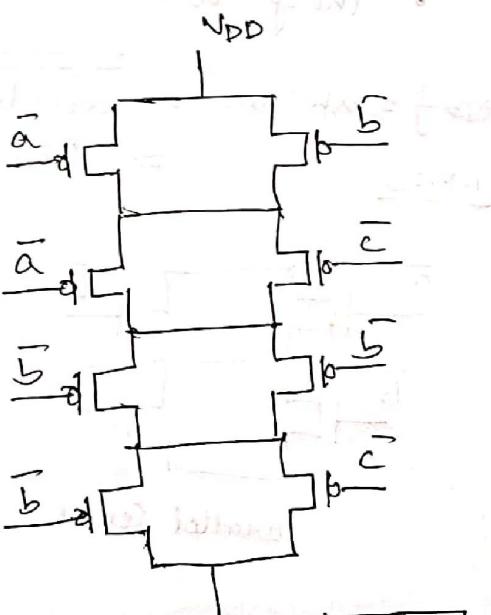
parallel series.



SP-PS.



SP-SP

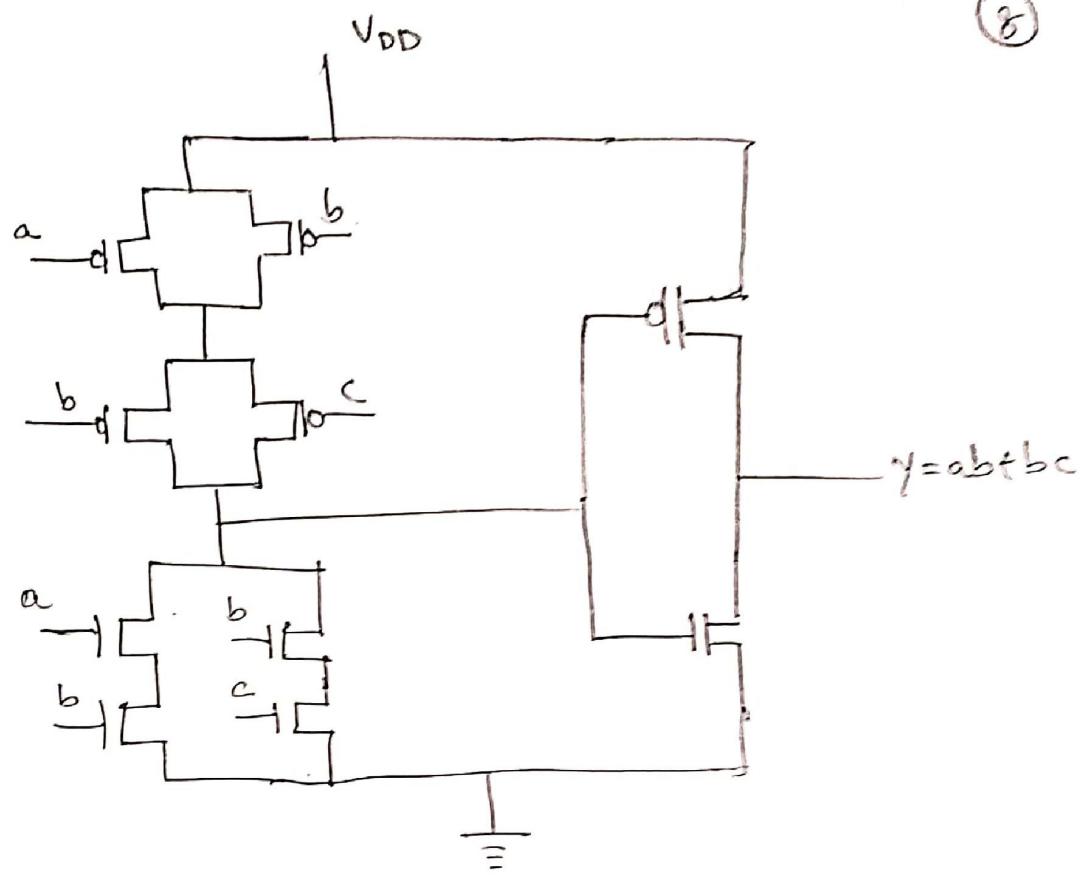


PS-PS.

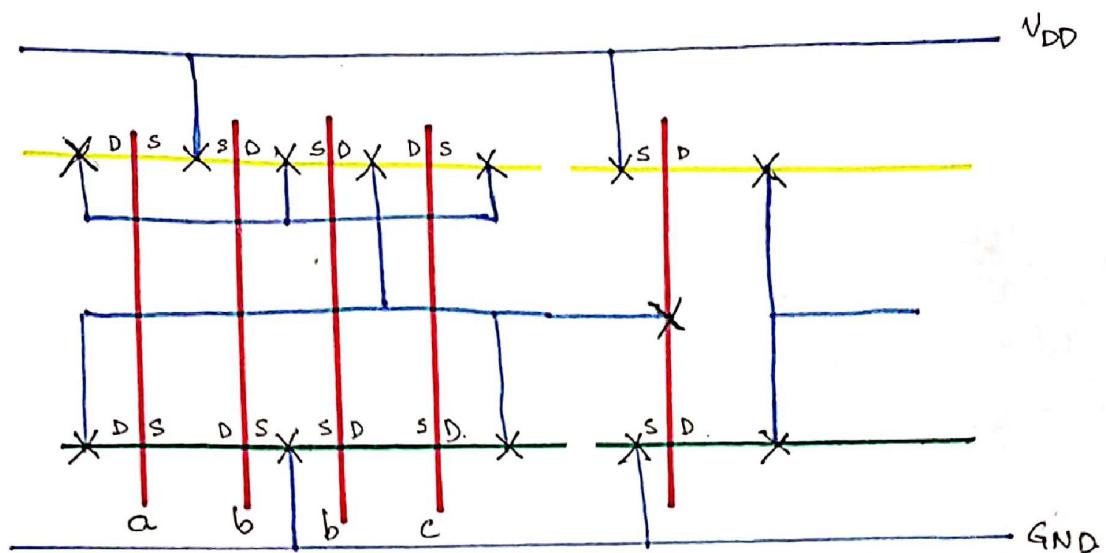
PS-SP

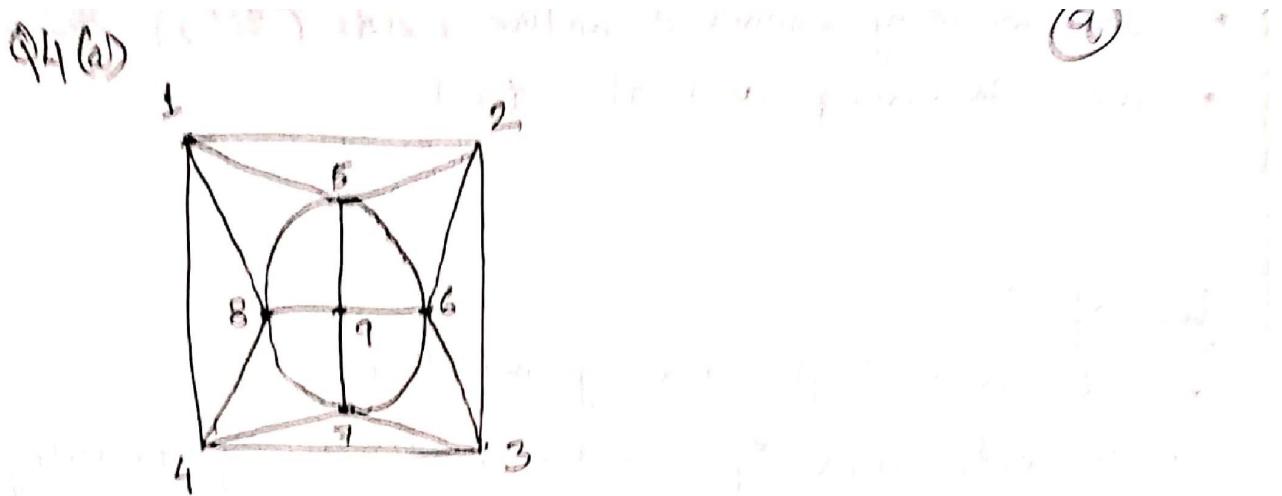
Q 3(b)

8

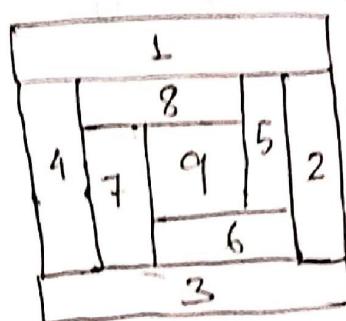


Stick diagram



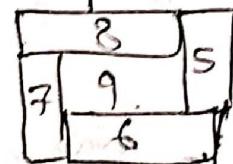
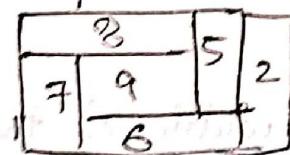
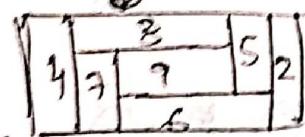
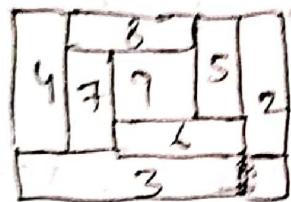
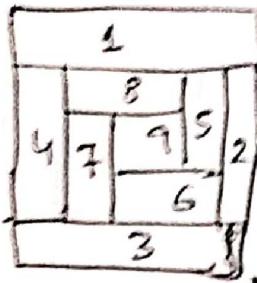


Rectangular Dual:



The given floor plan is not sliceable. We can initially divide the floor plan but later it is not possible.

(10)

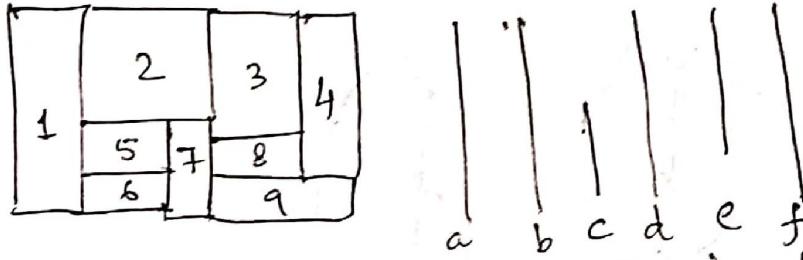


∴ The whole  
floorplan is  
not ~~sliceable~~  
sliceable.

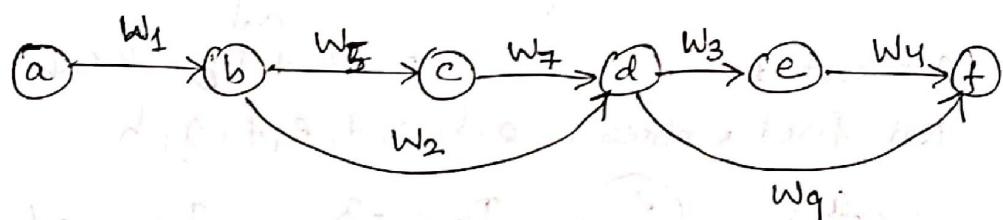
This floorplan is no  
longer sliceable.

Q4(b)

(11)



In horizontal dependency graph each junction is represented as a vertex. Let  $w_i$  denote the width of chip  $i$ .



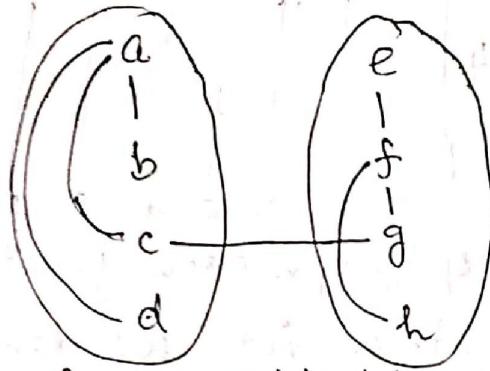
~~width of chip( $W$ ) = Longest path from left to right.~~

$$W = w_1 + \max(w_5 + w_7, w_2) + \max(w_3 + w_4, w_9)$$

$W$  is the minimum width of the chip.

Q5 (a)

(7)



$c_{ab} = 1$  if edge exists b/w a, b else 0.

$E_a$  be the external cost of vertex a.

$I_a$  be the internal cost of vertex a.

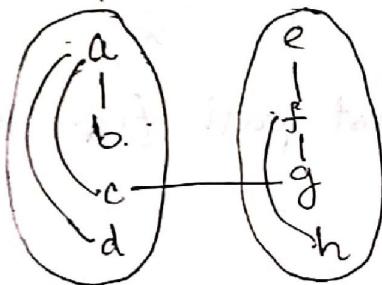
$g_{ab}$  = gain in swapping vertices a, b.

$$D_a = E_a - I_a$$

$$= D_a + D_b - 2c_{ab}$$

④ Cut cost 1

Not fixed vertices: a, b, c, d, e, f, g, h.



$$D_a = -3$$

$$D_e = -1$$

$$D_b = -1$$

$$D_f = -3$$

$$D_c = 0$$

$$D_g = 0$$

$$D_d = -1$$

$$D_h = -1$$

$$g_{ae} = -4$$

$$g_{be} = -2$$

$$g_{ce} = -1$$

$$g_{af} = -6$$

$$g_{bf} = -4$$

$$g_{cf} = -3$$

$$g_{ag} = -3$$

$$g_{bg} = -1$$

$$g_{cg} = -2$$

$$g_{ah} = -4$$

$$g_{bh} = -2$$

$$g_{ch} = -1$$

$$g_{de} = -2$$

choose the one with maximum

$$g_{df} = -4$$

gain  $\therefore g_{de} = g_{fg} = g_{ch} = g_{dg} = -1$

$$g_{dg} = -1$$

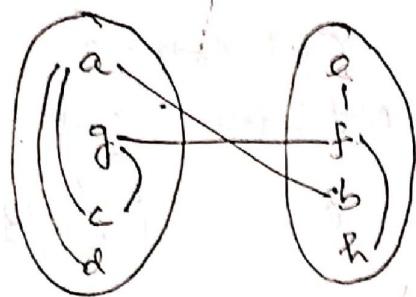
: we can choose any one.

$$g_{dh} = -2$$

Say, we swap b, g.

$$g_1 = -1$$

② Swap b, g



Cut cost: 2

Not fixed: a, c, d, e, f, h

$$D'_a = -1$$

$$D'_e = -1$$

~~$D'_b = 0$~~   $D'_c = -2$

$$D'_f = -1$$

$$D'_d = -1$$

$$D'_h = -1$$

$$g'_{ae} = -2$$

$$g'_{ce} = -3$$

$$g'_{de} = -2$$

$$g'_{af} = -2$$

$$g'_{cf} = -3$$

$$g'_{df} = -2$$

$$g'_{ah} = -2$$

$$g'_{ch} = -3$$

$$g'_{dh} = -2$$

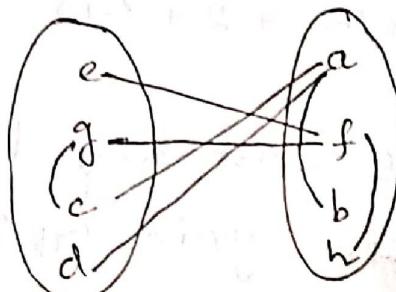
$$g'_2 = -2$$

Now swap a, e.

③ Swap a, e.

Cut cost: 4

Not fixed: e, d, f, h



$$D''_c = 0 \quad D''_f = 1$$

$$D''_d = 1 \quad D''_h = -1$$

$$g''_{cf} = 1$$

$$g''_{af} = 2$$

$$g''_{ch} = -1$$

$$g''_{dh} = 0$$

$$\max \text{ gain} = g''_{af} = 2 \quad \therefore \text{swap d, f.}$$

$$g_3 = 2$$

(4) Swap d,f



Cut cost: 2  
Not fixed: g, h.

$$D_c''' = 0$$

$$D_h''' = 1$$

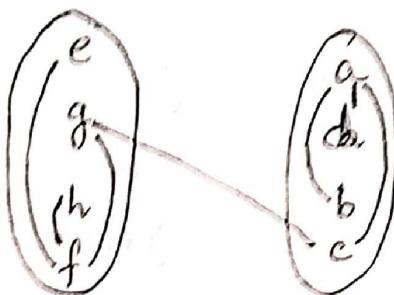
$$g_{ch}''' = 1$$

$$g_4''' = 1$$

(5) Swap c,h.

Cut cost: 1  
Not fixed: -

6



This is one pass of the K-L Algorithm.

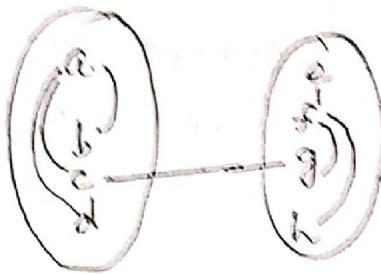
$$\begin{aligned}\text{Total gain } G &= \cancel{g_1 + g_2} \sum g_i \\ &= -1 + (-2) + 2 + (1) \\ &= 0\end{aligned}$$

$\therefore$  There does not exist any k for which the cumulative gain  $G_k > 0$

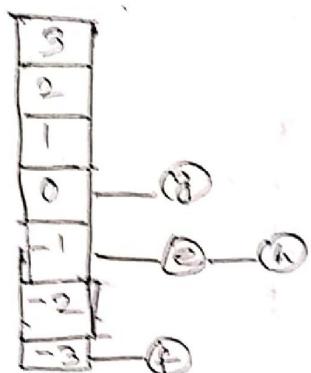
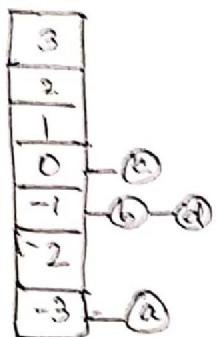
$\therefore$  The original ~~part~~ partition is optimal in itself.

Q5(b)

15



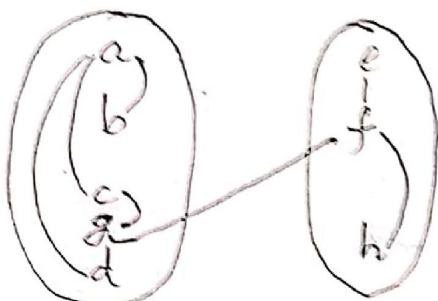
①



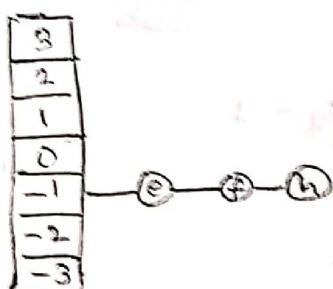
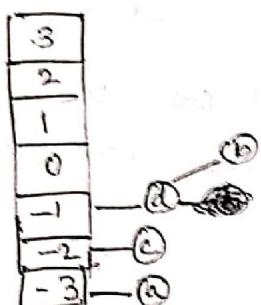
Fixed: —  
cut cost: 1

Now swap max gain. Say, ~~move~~ <sup>move</sup> g

② Move g. ~~f~~ <sup>g</sup> = 0 (Gain)

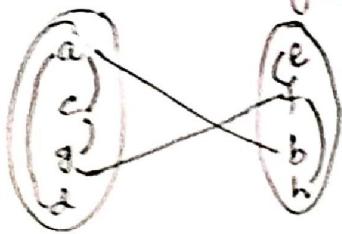


fixed : g  
cut cost = 1



move b

③ move b



$$g(2) = \cancel{g_2} = -1$$

Cut cost: 2

Fixed: g, b.

3
2
1
0
-1
-2
-3

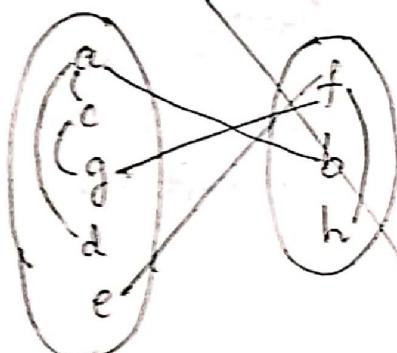
3
2
1
0
-1
-2
-3

④ move e

~~$$g(3) = \cancel{g_3} = -1$$~~

Cut cost: 3

Fixed: g, b, e.



3
2
1
0
-1
-2
-3

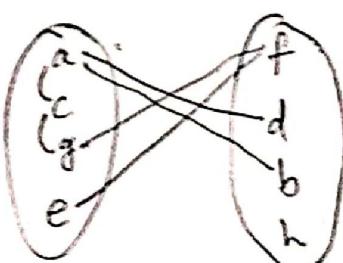
3
2
1
0
-1
-2
-3

⑤ move d.

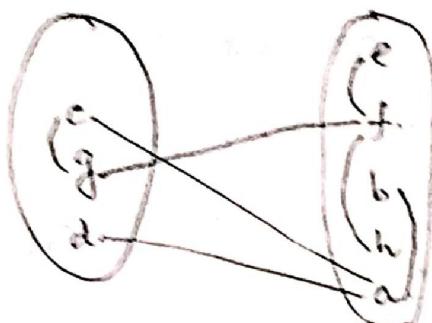
$$g_4 = 1$$

Cut cost: 2

Fixed: g, b, e, d.



④ move a.  $g_4 = -1$  cut cost : 3  
Fixed: g, b, c, e

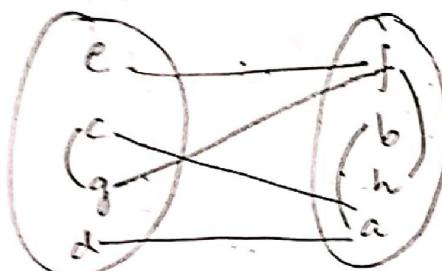


3	①
2	
1	②
0	③
-1	
-2	
-3	

3	①
2	
1	②
0	③
-1	④
-2	⑤
-3	⑥

Now d has max. gain but if we swap d  
then balance will be lost.  
 $\therefore$  we have to swap from other partition.

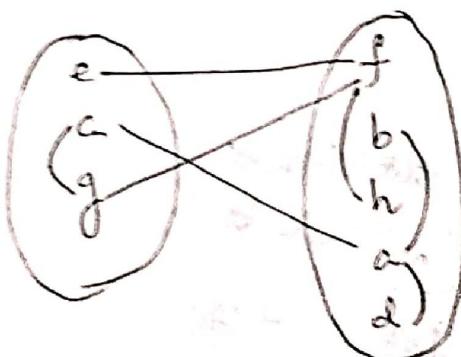
⑤ move e.  $g_4 = -1$  cut cost : 4.  
Fixed: g, b, a, e



3	②
2	
1	③
0	④
-1	
-2	
-3	

3	④
2	
1	⑤
0	⑥
-1	⑦
-2	
-3	

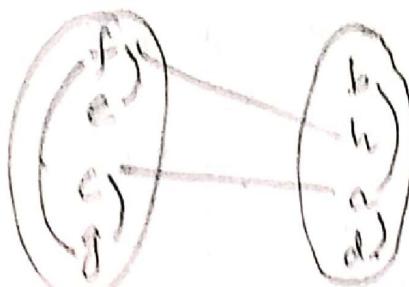
⑥ move d.  $g_5 = 1$  fixed: g, b, a, e, d  
cutcost : 3.



3	③
2	
1	④
0	⑤
-1	
-2	
-3	

3	⑤
2	
1	⑥
0	⑦
-1	
-2	
-3	

(1) Move f  $\rightarrow g_1 = 1$       Fixed: g, h, a, e, d, f  
 cut cost: 2

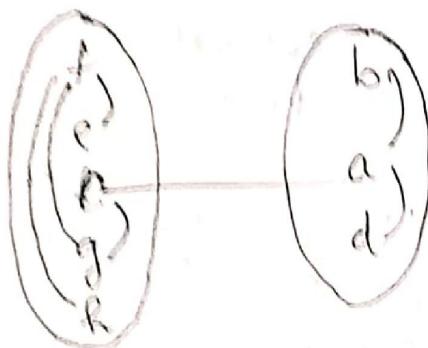


3	
2	
1	
0	→ C
-1	
-2	
-3	

3	
2	
1	
0	→ C
-1	
-2	
-3	

(2) move h  $\rightarrow g_2 = 1$       fixed: g, b, a, e, d, f, h  
 cut cost: 1.

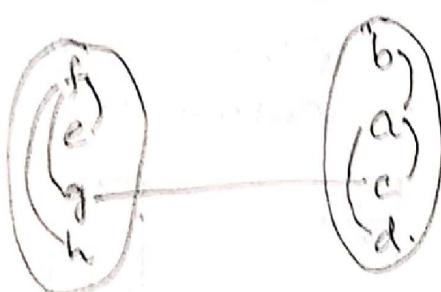


3	
2	
1	
0	→ C
-1	
-2	
-3	

3	
2	
1	
0	
-1	
-2	
-3	

(3) move e  $\rightarrow g_3 = 0$ .      fixed: g, b, a, e, d, f, h, c  
 cut cost = 1.



fixed: g, b, a, e, d, f, h, c

cut cost = 1.

Total cumulative gain  $\sum g_k$  <sup>such effect</sup>

$$G = g_1 + g_2 + g_3 + \dots + g_8$$

$$= 0.$$

∴ Initial partition was optimal.